

## Description

The HSS2N15 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

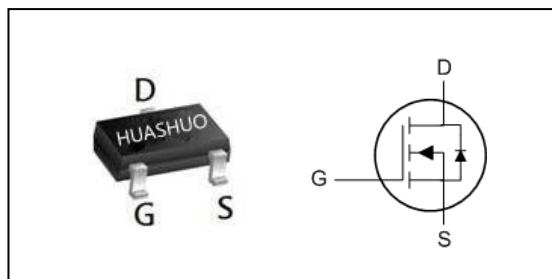
The HSS2N15 meet the RoHS and Green Product requirement with full function reliability approved.

## Product Summary

V <sub>DS</sub>	150	V
R <sub>DS(ON),max</sub>	280	mΩ
I <sub>D</sub>	1.8	A

- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

## SOT23 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	150	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	1.8	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	1.4	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	7.2	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	1.3	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>	---	100	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	80	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu\text{A}$	150	---	---	V
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=2A$	---	240	280	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=1A$	---	250	300	
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$	1.0	2	2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=150V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
$I_{DSs}$	Drain-Source Leakage Current	$V_{DS}=150V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	30	$\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$Q_g$	Total Gate Charge (10V)	$V_{DS}=75V, V_{GS}=10V, I_D=2A$	---	18	---	nC
$Q_{gs}$	Gate-Source Charge		---	4.6	---	
$Q_{gd}$	Gate-Drain Charge		---	5.7	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=75V, V_{GS}=10V, R_G=6\Omega$	---	13	---	ns
$T_r$	Rise Time		---	19	---	
$T_{d(off)}$	Turn-Off Delay Time		---	26	---	
$T_f$	Fall Time		---	9	---	
$C_{iss}$	Input Capacitance	$V_{DS}=75V, V_{GS}=0V, f=1\text{MHz}$	---	840	---	pF
$C_{oss}$	Output Capacitance		---	119	---	
$C_{rss}$	Reverse Transfer Capacitance		---	25	---	

**Diode Characteristics**

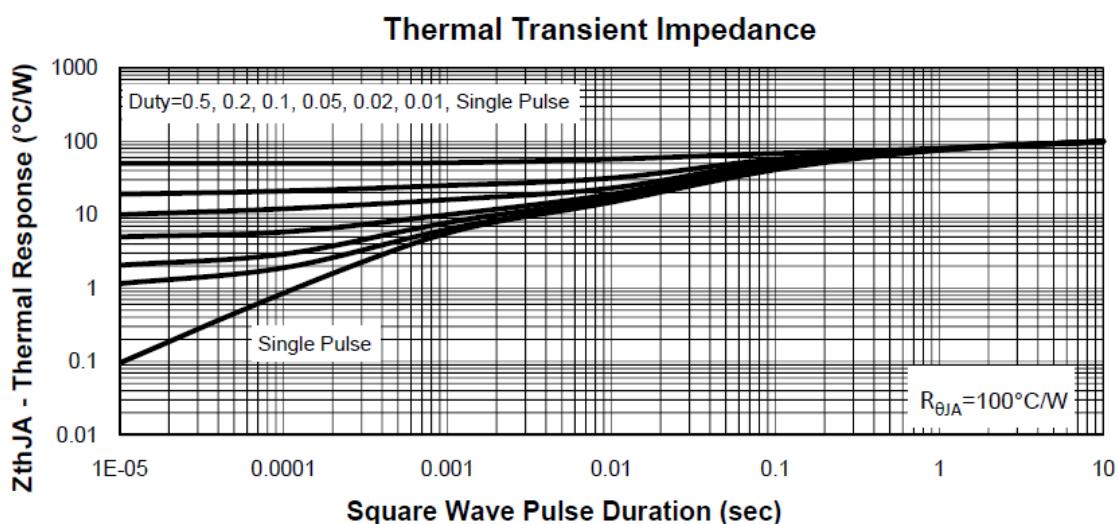
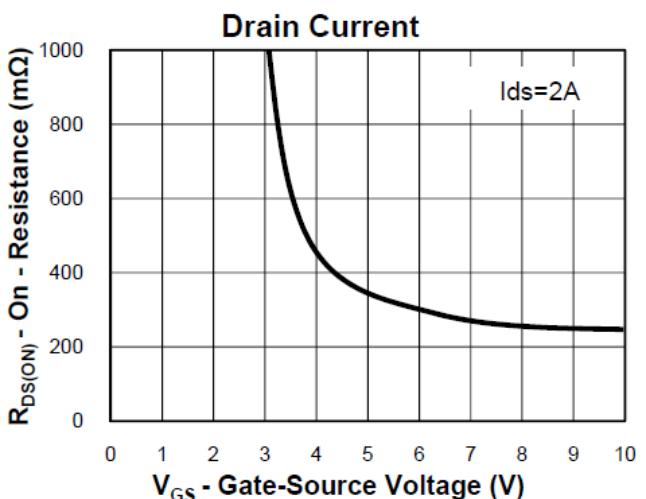
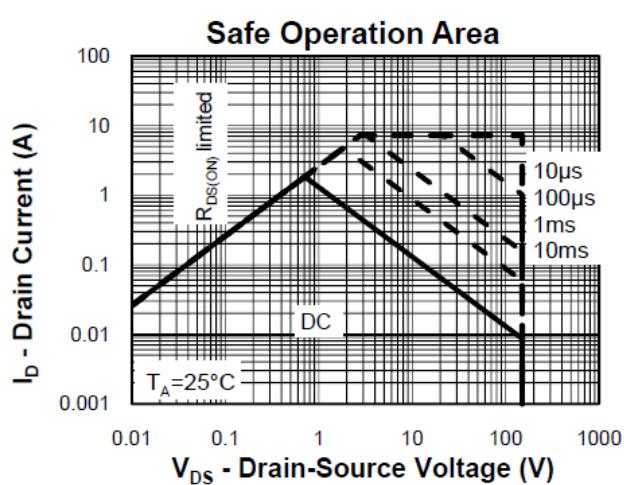
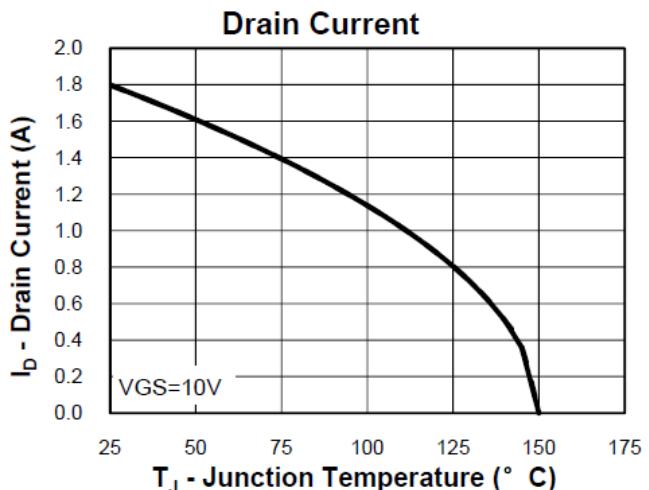
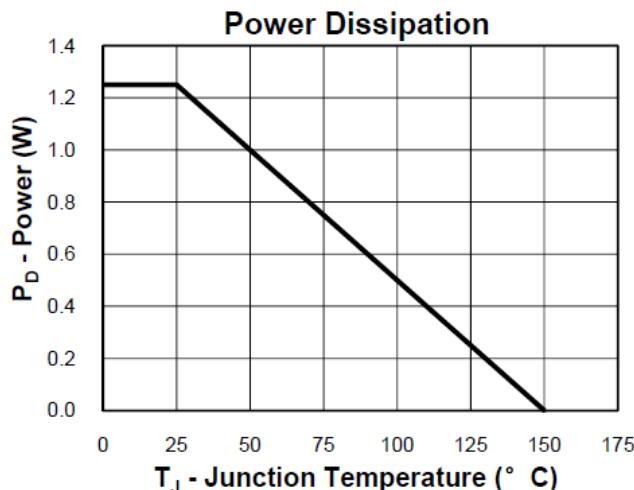
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_s$	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V$ , Force Current	---	---	1.8	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_s=1A, T_J=25^\circ\text{C}$	---	---	1.2	V

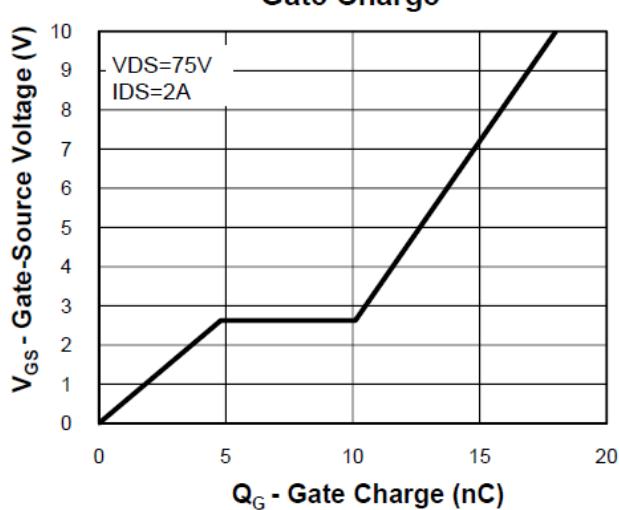
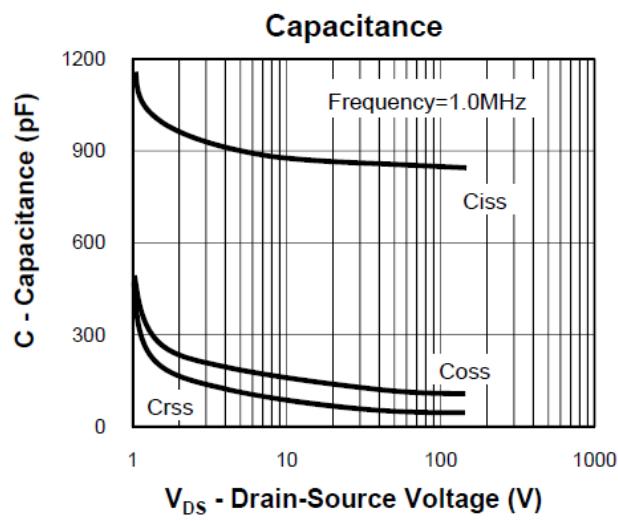
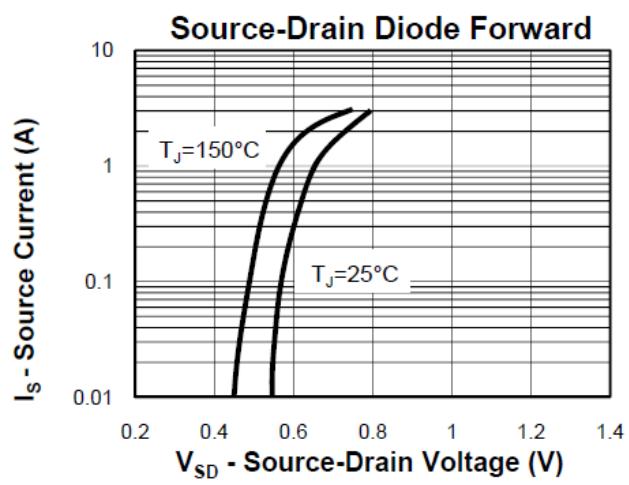
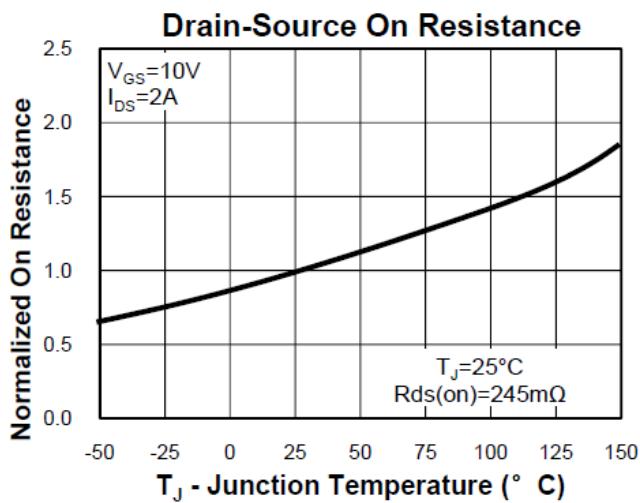
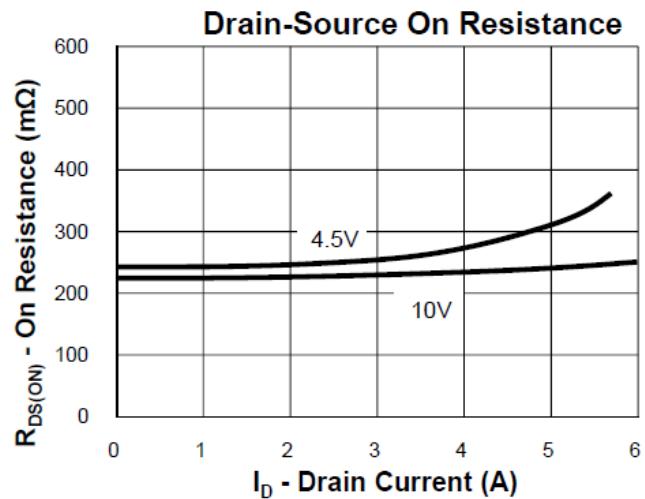
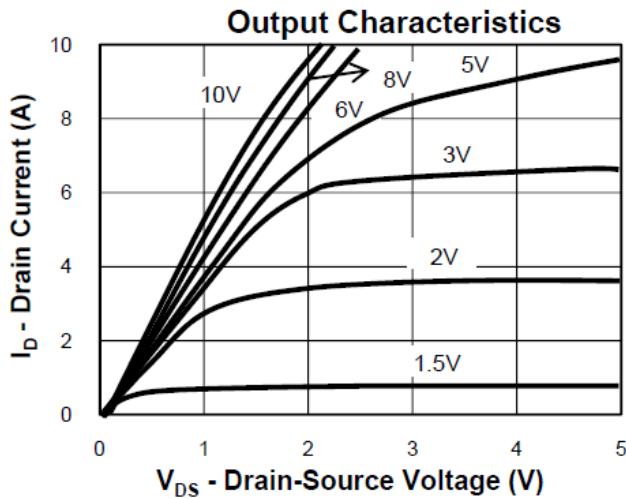
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



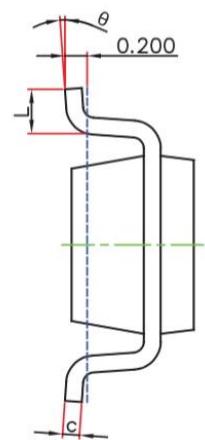
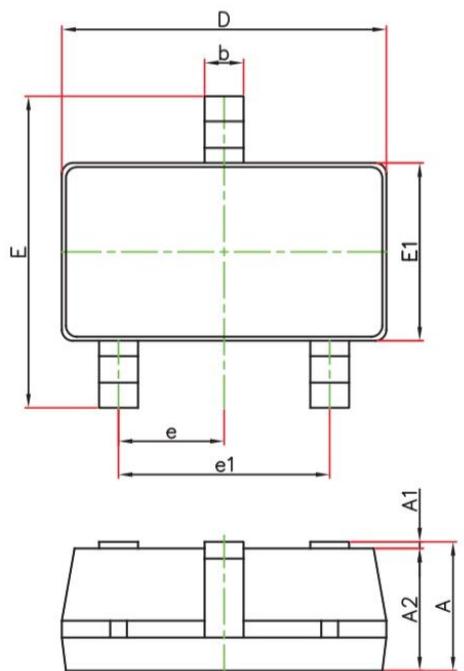
### Typical Characteristics





## Ordering Information

Part Number	Package code	Packaging
HSS2N15	SOT-23L	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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